



**THE DATASHEET OF
BAW62,143**



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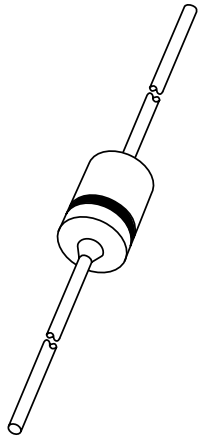
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Kind regards,

Team Nexperia

DATA SHEET



BAW62 High-speed diode

Product data sheet
Supersedes data of April 1996

1996 Sep 17

High-speed diode

BAW62

FEATURES

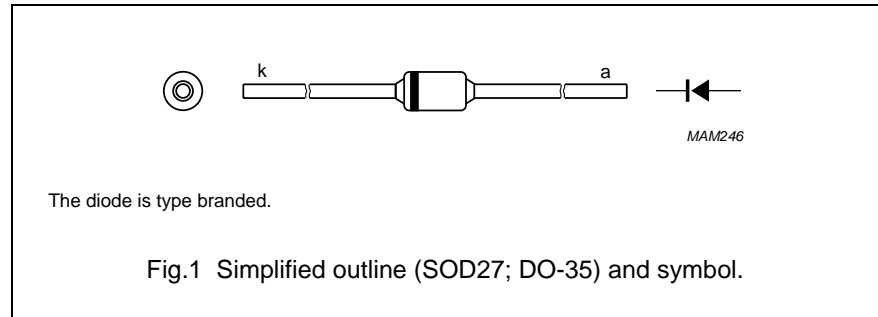
- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching
- Fast logic applications.

DESCRIPTION

The BAW62 is a high-speed switching diode fabricated in planar technology, and encapsulated in the hermetically sealed leaded glass SOD27 (DO-35) package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|---------------|-------------|
| V _R | continuous reverse voltage | | – | 75 | V |
| V _{RRM} | repetitive peak reverse voltage | | – | 75 | V |
| I _F | continuous forward current | see Fig.2; note 1 | – | 250 | mA |
| I _{FRM} | repetitive peak forward current | | – | 450 | mA |
| I _{FSM} | non-repetitive peak forward current | square wave; T _j = 25 °C prior to surge; see Fig.4 t = 1 μs t = 1 ms t = 1 s | – | 4 1 0.5 | A A A |
| P _{tot} | total power dissipation | T _{amb} = 25 °C; note 1 | – | 350 | mW |
| T _{stg} | storage temperature | | –65 | +200 | °C |
| T _j | junction temperature | | – | 200 | °C |

Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

High-speed diode

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ELECTRICAL CHARACTERISTICST_j = 25 °C; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------------|--------------------------|---|------|------|------|
| V _F | forward voltage | see Fig.3 | | | |
| | | I _F = 5 mA | 620 | 750 | mV |
| | | I _F = 100 mA | – | 1000 | mV |
| | | I _F = 100 mA; T _j = 100 °C | – | 930 | mV |
| I _R | reverse current | see Fig.5 | | | |
| | | V _R = 20 V | – | 25 | nA |
| | | V _R = 50 V | – | 200 | nA |
| | | V _R = 75 V | – | 5 | μA |
| | | V _R = 20 V; T _j = 150 °C | – | 50 | μA |
| | | V _R = 75 V; T _j = 150 °C | – | 100 | μA |
| C _d | diode capacitance | f = 1 MHz; V _R = 0; see Fig.6 | – | 2 | pF |
| t _{rr} | reverse recovery time | when switched from I _F = 10 mA to I _R = 10 mA; R _L = 100 Ω; measured at I _R = 1 mA; see Fig.7 | – | 4 | ns |
| V _{fr} | forward recovery voltage | when switched from I _F = 50 mA; t _r = 20 ns; see Fig.8 | – | 2.5 | V |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|---------------------------|-------|------|
| R _{th j-tp} | thermal resistance from junction to tie-point | lead length 10 mm | 240 | K/W |
| R _{th j-a} | thermal resistance from junction to ambient | lead length 10 mm; note 1 | 500 | K/W |

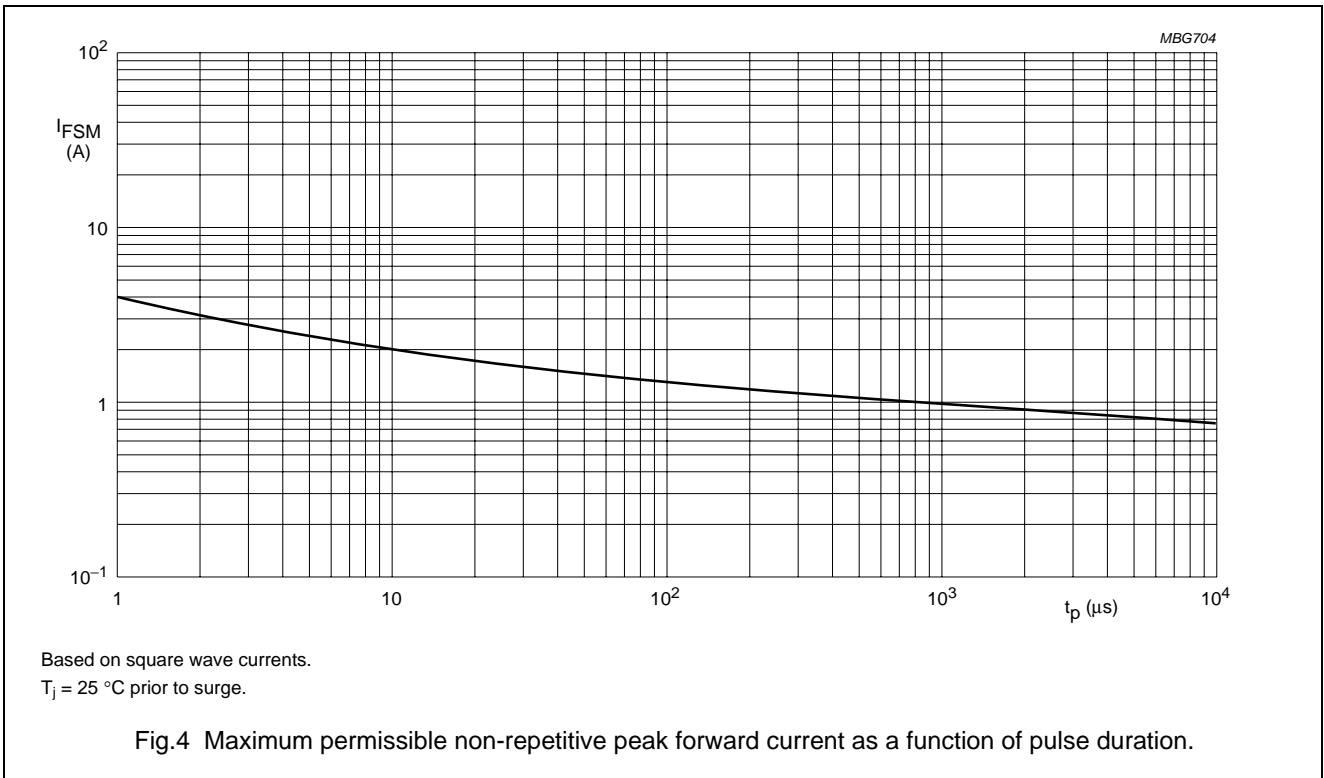
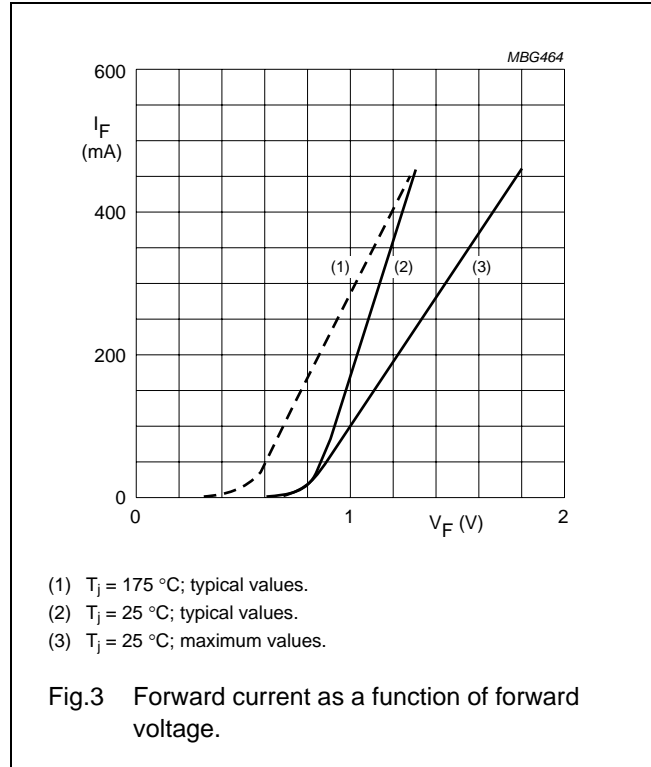
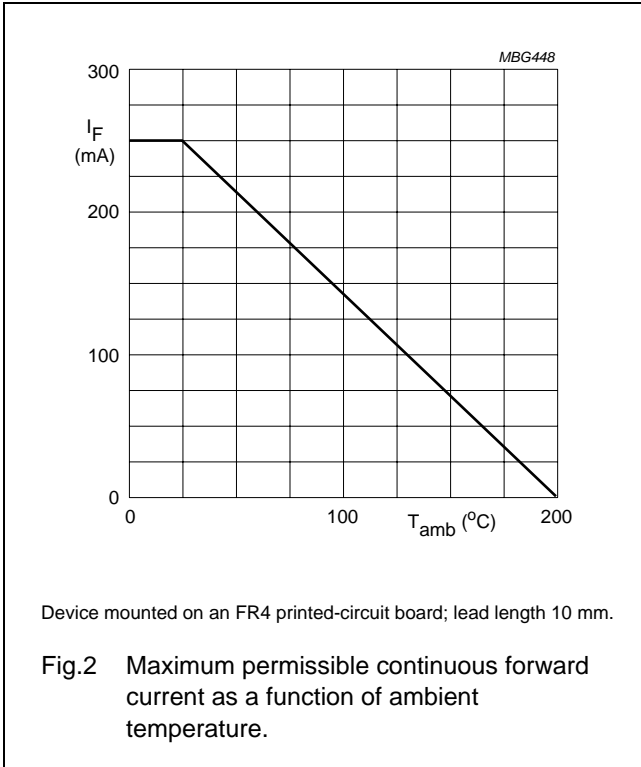
Note

1. Device mounted on a printed circuit-board without metallization pad.

High-speed diode

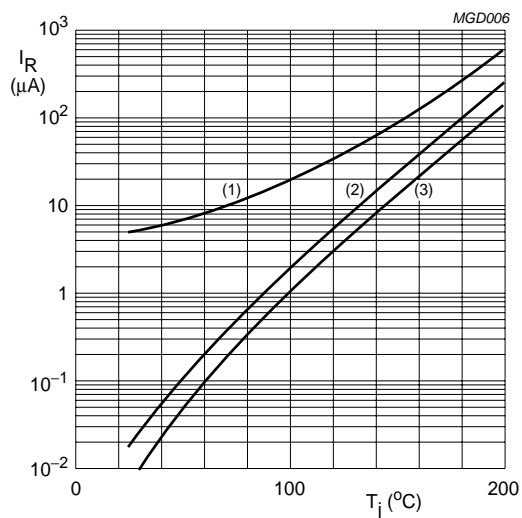
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GRAPHICAL DATA



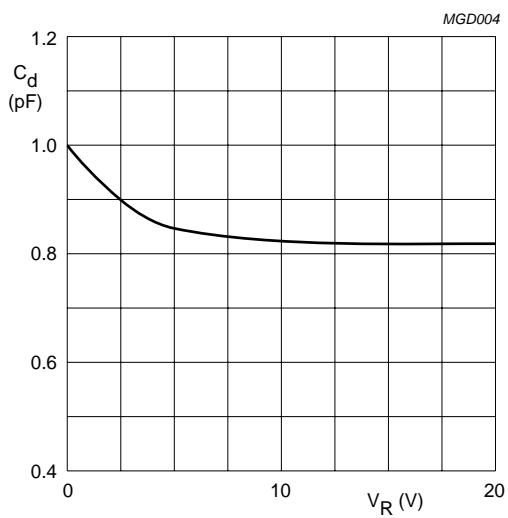
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- (1) $V_R = 75$ V; maximum values.
- (2) $V_R = 75$ V; typical values.
- (3) $V_R = 20$ V; typical values.

Fig.5 Reverse current as a function of junction temperature.

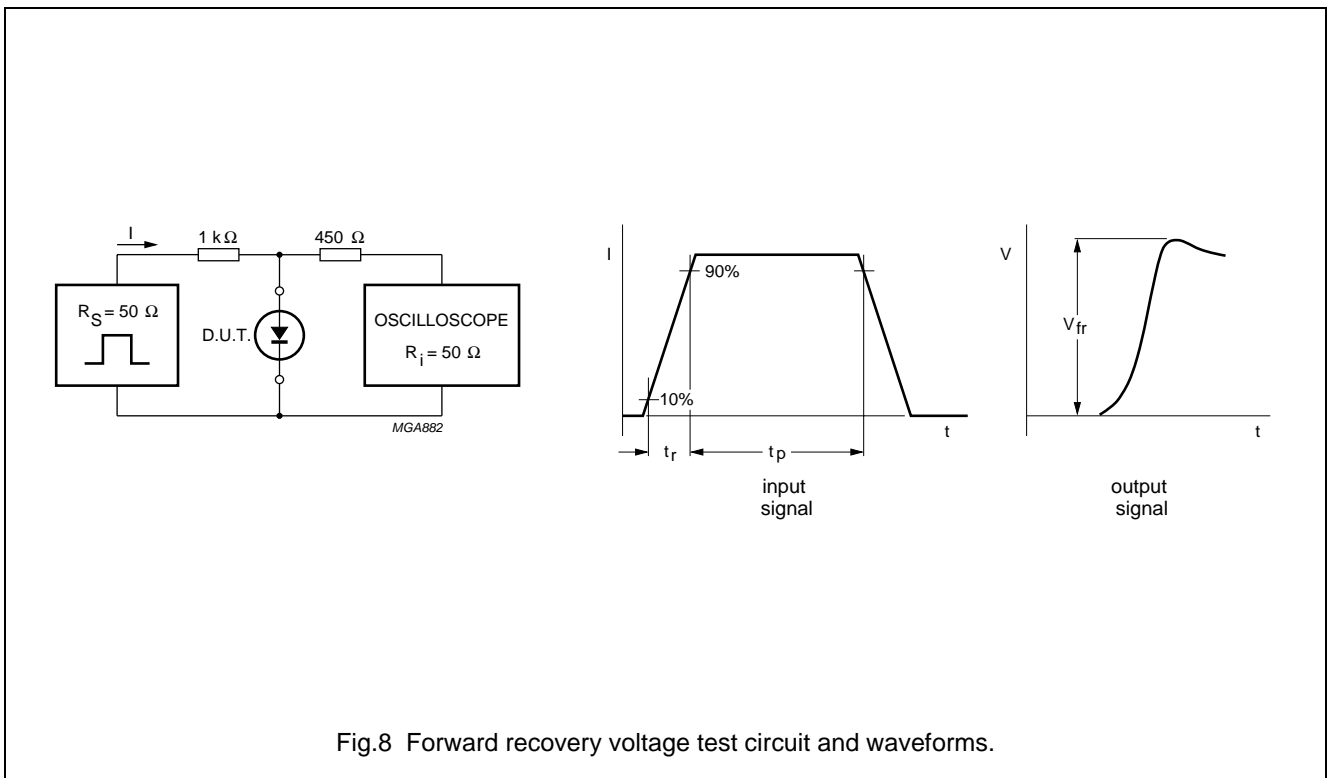
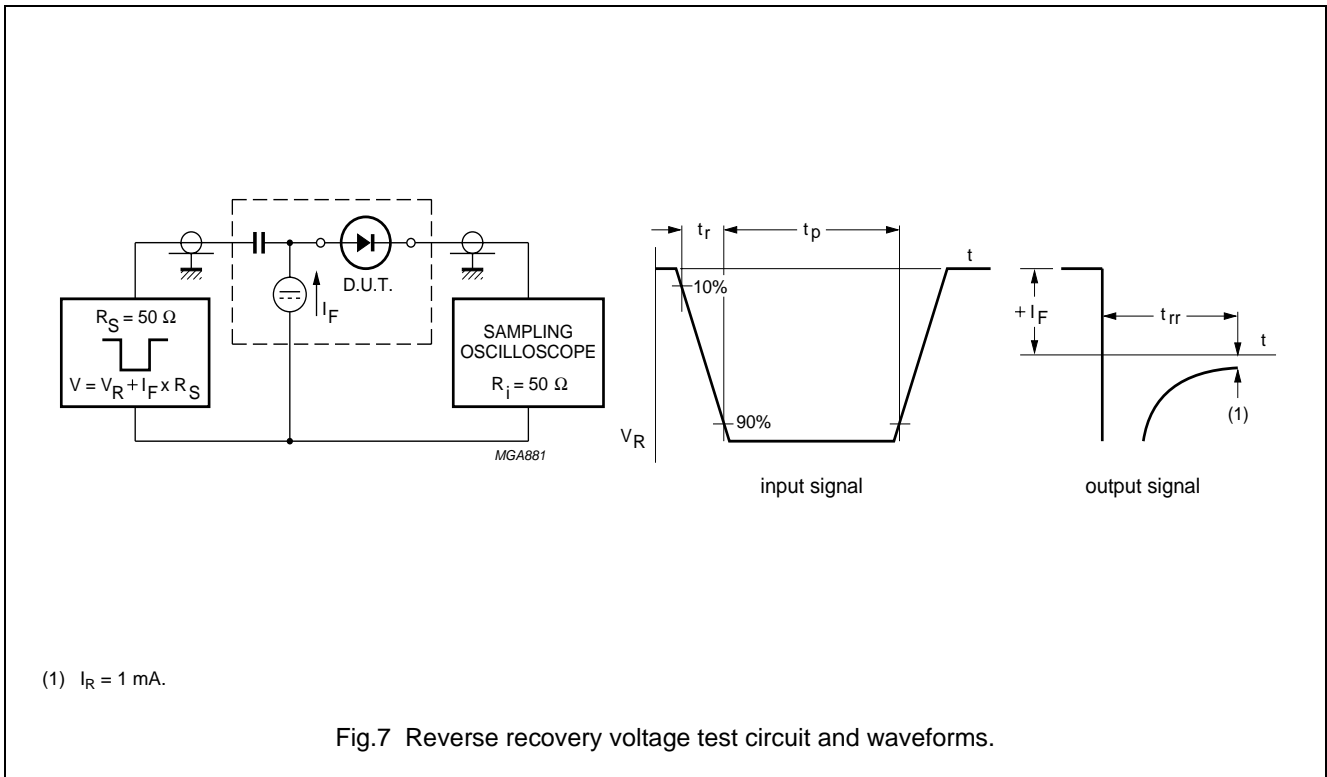


$f = 1$ MHz; $T_j = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diode

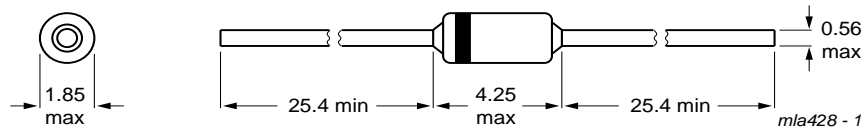
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High-speed diode

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PACKAGE OUTLINE



Dimensions in mm.

Fig.9 SOD27 (DO-35).

High-speed diode

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

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Contact information

For additional information please visit: **<http://www.nxp.com>**

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